

Timo Sajavaara

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

223 papers	6,726 citations	48 h-index	73 g-index
241 ext. papers	7,198 ext. citations	3.5 avg, IF	5.42 L-index

#	Paper	IF	Citations
223	Nanorod orientation control by swift heavy ion irradiation. <i>Applied Physics Letters</i> , 2022 , 120, 171602	3.4	1
222	Spatial ALD of Al ₂ O ₃ and ZnO using heavy water. <i>Surface and Coatings Technology</i> , 2022 , 441, 128456	4.4	1
221	Atomic layer deposition of ternary ruthenates by combining metalorganic precursors with RuO as the co-reactant. <i>Dalton Transactions</i> , 2021 ,	4.3	1
220	Al ₂ O ₃ ALD films grown using TMA + rare isotope ² H ₂ ¹⁶ O and ¹ H ₂ ¹⁸ O precursors. <i>Applied Surface Science</i> , 2021 , 546, 148909	6.7	8
219	Hydrogen and Deuterium Incorporation in ZnO Films Grown by Atomic Layer Deposition. <i>Coatings</i> , 2021 , 11, 542	2.9	2
218	Phosphites as precursors in atomic layer deposition thin film synthesis. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021 , 39, 032404	2.9	2
217	Atomic scale surface modification of TiO ₂ 3D nano-arrays: plasma enhanced atomic layer deposition of NiO for photocatalysis. <i>Materials Advances</i> , 2021 , 2, 273-279	3.3	1
216	What Determines the Electrochemical Properties of Nitrogenated Amorphous Carbon Thin Films?. <i>Chemistry of Materials</i> , 2021 , 33, 6813-6824	9.6	2
215	Mechanical and optical properties of as-grown and thermally annealed titanium dioxide from titanium tetrachloride and water by atomic layer deposition. <i>Thin Solid Films</i> , 2021 , 732, 138758	2.2	7
214	A liquid alkoxide precursor for the atomic layer deposition of aluminum oxide films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2020 , 38, 022417	2.9	1
213	Antiferromagnetism and p-type conductivity of nonstoichiometric nickel oxide thin films. <i>Information Materials</i> , 2020 , 2, 769-774	23.1	8
212	The co-reactant role during plasma enhanced atomic layer deposition of palladium. <i>Physical Chemistry Chemical Physics</i> , 2020 , 22, 9124-9136	3.6	3
211	Characterization of ²³³ U alpha recoil sources for ²²⁹ (m)Th beam production. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2020 , 463, 441-448	1.2	3
210	Experimental evidence on photo-assisted O ⁺ ion production from Al ₂ O ₃ cathode in cesium sputter negative ion source. <i>Journal of Applied Physics</i> , 2020 , 128, 094903	2.5	2
209	Ti Alloyed -GaO: Route towards Wide Band Gap Engineering. <i>Micromachines</i> , 2020 , 11,	3.3	6
208	Atomic Layer Deposition of Localized Boron- and Hydrogen-Doped Aluminum Oxide Using Trimethyl Borate as a Dopant Precursor. <i>Chemistry of Materials</i> , 2020 , 32, 4152-4165	9.6	1
207	Thermal atomic layer deposition of AlO _x N _y thin films for surface passivation of nano-textured flexible silicon. <i>Solar Energy Materials and Solar Cells</i> , 2019 , 193, 231-236	6.4	13

206	A new beamline for energy-dispersive high-resolution PIXE analysis using polycapillary optics. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2019 , 447, 59-67	1.2	3
205	In-situ annealing characterization of atomic-layer-deposited Al ₂ O ₃ in N ₂ , H ₂ and vacuum atmospheres. <i>Thin Solid Films</i> , 2019 , 682, 147-155	2.2	3
204	Room-Temperature Micropillar Growth of Lithium-Titanate-Carbon Composite Structures by Self-Biased Direct Current Magnetron Sputtering for Lithium Ion Microbatteries. <i>Advanced Functional Materials</i> , 2019 , 29, 1904306	15.6	4
203	Aluminum tri-isopropoxide as an alternative precursor for atomic layer deposition of aluminum oxide thin films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2019 , 37, 0409019	2.9	3
202	Structural and Optical Characterization of ZnS Ultrathin Films Prepared by Low-Temperature ALD from Diethylzinc and 1,5-Pentanedithiol after Various Annealing Treatments. <i>Materials</i> , 2019 , 12,	3.5	7
201	Nanoscale etching of III-V semiconductors in acidic hydrogen peroxide solution: GaAs and InP, a striking contrast in surface chemistry. <i>Applied Surface Science</i> , 2019 , 465, 596-606	6.7	8
200	High quality superconducting titanium nitride thin film growth using infrared pulsed laser deposition. <i>Superconductor Science and Technology</i> , 2018 , 31, 055017	3.1	19
199	Atomic layer deposition of AlN from AlCl ₃ using NH ₃ and Ar/NH ₃ plasma. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2018 , 36, 021508	2.9	15
198	Tribological properties of thin films made by atomic layer deposition sliding against silicon. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2018 , 36, 01A122	2.9	7
197	Low-temperature atomic layer deposition of SiO ₂ /Al ₂ O ₃ multilayer structures constructed on self-standing films of cellulose nanofibrils. <i>Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences</i> , 2018 , 376,	3	8
196	Comparison of mechanical properties and composition of magnetron sputter and plasma enhanced atomic layer deposition aluminum nitride films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2018 , 36, 051508	2.9	7
195	Properties of Atomic Layer Deposited Nanolaminates of Zirconium and Cobalt Oxides. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, P402-P409	2	
194	Atomic layer deposition of Ti-Nb-O thin films onto electrospun fibers for fibrous and tubular catalyst support structures. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2018 , 36, 01A102	2.9	6
193	Heavy ion induced Ti X-ray satellite structure for Ti, TiN, and TiO ₂ thin films. <i>X-Ray Spectrometry</i> , 2018 , 47, 475-483	0.9	1
192	Nanoscale Etching of GaAs and InP in Acidic H ₂ O ₂ Solution: A Striking Contrast in Kinetics and Surface Chemistry. <i>Solid State Phenomena</i> , 2018 , 282, 48-51	0.4	1
191	The α - and β -plasma modes in plasma-enhanced atomic layer deposition with O ₂ /N ₂ capacitive discharges. <i>Journal Physics D: Applied Physics</i> , 2017 , 50, 095201	3	5
190	Energy loss and straggling of MeV Si ions in gases. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2017 , 391, 20-26	1.2	
189	Generalized Noise Study of Solid-State Nanopores at Low Frequencies. <i>ACS Sensors</i> , 2017 , 2, 300-307	9.2	42

188	Conceptual study of a heavy-ion-ERDA spectrometer for energies below 6 MeV. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2017 , 406, 61-65	1.2	3
187	Minimum detection limits and applications of proton and helium induced X-ray emission using transition-edge sensor array. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2017 , 406, 130-134	1.2	3
186	Oxy-nitrides characterization with a new ERD-TOF system. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2017 , 406, 112-114	1.2	6
185	Thin film growth into the ion track structures in polyimide by atomic layer deposition. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2017 , 406, 156-160	1.2	
184	Characterization of ALD grown TixAlyN and TixAlyC thin films. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2017 , 406, 152-155	1.2	3
183	Ozone-Based Atomic Layer Deposition of Al ₂ O ₃ from Dimethylaluminum Chloride and Its Impact on Silicon Surface Passivation. <i>Advanced Electronic Materials</i> , 2017 , 3, 1600491	6.4	10
182	Aluminum oxide/titanium dioxide nanolaminates grown by atomic layer deposition: Growth and mechanical properties. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2017 , 35, 01B105	2.9	28
181	Review Article: Recommended reading list of early publications on atomic layer deposition Outcome of the Virtual Project on the History of ALD <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2017 , 35, 010801	2.9	55
180	Blistering mechanisms of atomic-layer-deposited AlN and Al ₂ O ₃ films. <i>Applied Physics Letters</i> , 2017 , 111, 141606	3.4	11
179	Low-Temperature Molecular Layer Deposition Using Monofunctional Aromatic Precursors and Ozone-Based Ring-Opening Reactions. <i>Langmuir</i> , 2017 , 33, 9657-9665	4	10
178	Stabilizing organic photocathodes by low-temperature atomic layer deposition of TiO ₂ . <i>Sustainable Energy and Fuels</i> , 2017 , 1, 1915-1920	5.8	33
177	Room-temperature plasma-enhanced atomic layer deposition of ZnO: Film growth dependence on the PEALD reactor configuration. <i>Surface and Coatings Technology</i> , 2017 , 326, 281-290	4.4	12
176	Tang dynasty (618-907) bowl measured with PIXE. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2017 , 406, 329-333	1.2	1
175	Characterization and Electrochemical Properties of Oxygenated Amorphous Carbon (a-C) Films. <i>Electrochimica Acta</i> , 2016 , 220, 137-145	6.7	15
174	Stability, sub-gap current, 1/f-noise, and elemental depth profiling of annealed Al:Mn-ALOX-Al normal metal-insulator-superconducting tunnel junctions. <i>AIP Advances</i> , 2016 , 6, 125026	1.5	0
173	Digitizing data acquisition and time-of-flight pulse processing for ToF-ERDA. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2016 , 366, 179-183	1.2	3
172	Mass calibration of the energy axis in ToF- E elastic recoil detection analysis. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2016 , 371, 153-155	1.2	3
171	Alkylsilyl compounds as enablers of atomic layer deposition: analysis of (Et ₃ Si) ₃ As through the GaAs process. <i>Journal of Materials Chemistry C</i> , 2016 , 4, 449-454	7.1	2

170	Simulations on time-of-flight ERDA spectrometer performance. <i>Review of Scientific Instruments</i> , 2016 , 87, 083309	1.7	3
169	Unusual stoichiometry control in the atomic layer deposition of manganese borate films from manganese bis(tris(pyrazolyl)borate) and ozone. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2016 , 34, 051515	2.9	2
168	Broadband Ultrahigh-Resolution Spectroscopy of Particle-Induced X Rays: Extending the Limits of Nondestructive Analysis. <i>Physical Review Applied</i> , 2016 , 6,	4.3	17
167	Structural and chemical analysis of annealed plasma-enhanced atomic layer deposition aluminum nitride films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2016 , 34, 041506	2.9	20
166	Coating and functionalization of high density ion track structures by atomic layer deposition. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2016 , 832, 254-258	1.2	1
165	Normal-Metal/Insulator/Superconductor Tunnel Junction With Atomic-Layer-Deposited Titanium Nitride as Superconductor. <i>IEEE Transactions on Applied Superconductivity</i> , 2015 , 25, 1-4	1.8	8
164	Excellent silicon surface passivation using dimethylaluminium chloride as Al source for atomic layer deposited Al ₂ O ₃ . <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015 , 212, 1795-1799	1.6	9
163	Low-Temperature Atomic Layer Deposition of Crystalline and Photoactive Ultrathin Hematite Films for Solar Water Splitting. <i>ACS Nano</i> , 2015 , 9, 11775-83	16.7	59
162	Determination of molecular stopping cross section of ¹² C, ¹⁶ O, ²⁸ Si, ³⁵ Cl, ⁵⁸ Ni, ⁷⁹ Br, and ¹²⁷ I in silicon nitride. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2015 , 360, 90-96	1.2	4
161	Effect of ozone concentration on silicon surface passivation by atomic layer deposited Al ₂ O ₃ . <i>Applied Surface Science</i> , 2015 , 357, 2402-2407	6.7	17
160	Nanotribological, nanomechanical and interfacial characterization of atomic layer deposited TiO ₂ on a silicon substrate. <i>Wear</i> , 2015 , 342-343, 270-278	3.5	11
159	Atomic layer deposited lithium aluminum oxide: (In)dependency of film properties from pulsing sequence. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2015 , 33, 01A101	2.9	17
158	Nucleation and growth of ZnO on PMMA by low-temperature atomic layer deposition. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2015 , 33, 01A128	2.9	24
157	Studies on atomic layer deposition of IRMOF-8 thin films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2015 , 33, 01A121	2.9	17
156	Thermal and plasma enhanced atomic layer deposition of SiO ₂ using commercial silicon precursors. <i>Thin Solid Films</i> , 2014 , 558, 93-98	2.2	50
155	Atomic Layer Deposition of Spinel Lithium Manganese Oxide by Film-Body-Controlled Lithium Incorporation for Thin-Film Lithium-Ion Batteries. <i>Journal of Physical Chemistry C</i> , 2014 , 118, 1258-1268	3.8	58
154	Secondary electron flight times and tracks in the carbon foil time pick-up detector. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2014 , 336, 55-62	1.2	5
153	Time-of-flight Energy spectrometer for elemental depth profiling [Jyväskylä] Design. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2014 , 337, 55-61	1.2	59

152	Antibacterial and barrier properties of oriented polymer films with ZnO thin films applied with atomic layer deposition at low temperatures. <i>Thin Solid Films</i> , 2014 , 562, 331-337	2.2	42
151	Trajectory bending and energy spreading of charged ions in time-of-flight telescopes used for ion beam analysis. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2014 , 325, 101-106	1.2	4
150	Time-of-flight ERD with a 200 mm ² Si ₃ N ₄ window gas ionization chamber energy detector. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2014 , 332, 271-274	1.2	8
149	Potku [New analysis software for heavy ion elastic recoil detection analysis. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2014 , 331, 34-41	1.2	88
148	New experimental molecular stopping cross section data of Al ₂ O ₃ , for heavy ions. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2014 , 332, 341-345	1.2	6
147	Aluminum oxide from trimethylaluminum and water by atomic layer deposition: The temperature dependence of residual stress, elastic modulus, hardness and adhesion. <i>Thin Solid Films</i> , 2014 , 552, 124-133	2.2	119
146	Transition-Edge Sensors for Particle Induced X-ray Emission Measurements. <i>Journal of Low Temperature Physics</i> , 2014 , 176, 285-290	1.3	13
145	Energy-loss straggling of 210 MeV/u Kr ions in gases. <i>European Physical Journal D</i> , 2013 , 67, 1	1.3	13
144	Studies on atomic layer deposition of MOF-5 thin films. <i>Microporous and Mesoporous Materials</i> , 2013 , 182, 147-154	5.3	58
143	Atomic layer deposition of Li _x Ti _y O _z thin films. <i>RSC Advances</i> , 2013 , 3, 7537-7542	3.7	46
142	Atomic layer deposition of ferroelectric LiNbO ₃ . <i>Journal of Materials Chemistry C</i> , 2013 , 1, 4283-4290	7.1	51
141	Influence of titanium-substrate roughness on CaF ₂ thin films grown by atomic layer deposition. <i>Thin Solid Films</i> , 2013 , 531, 26-31	2.2	6
140	Low temperature atomic layer deposition of noble metals using ozone and molecular hydrogen as reactants. <i>Thin Solid Films</i> , 2013 , 531, 243-250	2.2	38
139	Atomic Layer Deposition of LiF Thin Films from Lithd, Mg(thd) ₂ , and TiF ₄ Precursors. <i>Chemistry of Materials</i> , 2013 , 25, 1656-1663	9.6	33
138	Advanced time-stamped total data acquisition control front-end for MeV ion beam microscopy and proton beam writing. <i>Microelectronic Engineering</i> , 2013 , 102, 9-11	2.5	3
137	Why are hydrogen ions best for MeV ion beam lithography?. <i>Microelectronic Engineering</i> , 2013 , 102, 22-24	2.5	5
136	High speed microfluidic prototyping by programmable proximity aperture MeV ion beam lithography. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2013 , 306, 302-306	1.2	4
135	Variation of lattice constant and cluster formation in GaAsBi. <i>Journal of Applied Physics</i> , 2013 , 114, 243504	5.4	44

134	Influence of plasma chemistry on impurity incorporation in AlN prepared by plasma enhanced atomic layer deposition. <i>Journal Physics D: Applied Physics</i> , 2013 , 46, 505502	3	27
133	Recent negative ion source activity at JYFL 2013 ,		8
132	Development of the Jyväskylä microbeam facility. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2012 , 272, 158-161	1.2	2
131	Lithography exposure characteristics of poly(methyl methacrylate) (PMMA) for carbon, helium and hydrogen ions. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2012 , 272, 162-164	1.2	15
130	Atomic layer deposition of Ru films from bis(2,5-dimethylpyrrolyl)ruthenium and oxygen. <i>Thin Solid Films</i> , 2012 , 520, 2756-2763	2.2	24
129	Atomic Layer Deposition of Osmium. <i>Chemistry of Materials</i> , 2012 , 24, 55-60	9.6	33
128	Evaluation and Comparison of Novel Precursors for Atomic Layer Deposition of Nb ₂ O ₅ Thin Films. <i>Chemistry of Materials</i> , 2012 , 24, 975-980	9.6	41
127	Atomic Layer Deposition of WO ₃ Thin Films using W(CO) ₆ and O ₃ Precursors. <i>Chemical Vapor Deposition</i> , 2012 , 18, 245-248		44
126	Evidence of quantum phase slip effect in titanium nanowires. <i>Physical Review B</i> , 2012 , 85,	3.3	50
125	Plasma etch characteristics of aluminum nitride mask layers grown by low-temperature plasma enhanced atomic layer deposition in SF ₆ based plasmas. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2012 , 30, 011504	2.9	11
124	Plasma-Enhanced Atomic Layer Deposition of Silver Thin Films. <i>Chemistry of Materials</i> , 2011 , 23, 2901-2907	9.6	89
123	Iridium metal and iridium oxide thin films grown by atomic layer deposition at low temperatures. <i>Journal of Materials Chemistry</i> , 2011 , 21, 16488		39
122	Depth profiling of Al ₂ O ₃ +TiO ₂ nanolaminates by means of a time-of-flight energy spectrometer. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2011 , 269, 3021-3024	1.2	13
121	Low Temperature Growth of High Purity, Low Resistivity Copper Films by Atomic Layer Deposition. <i>Chemistry of Materials</i> , 2011 , 23, 4417-4419	9.6	66
120	Properties of AlN grown by plasma enhanced atomic layer deposition. <i>Applied Surface Science</i> , 2011 , 257, 7827-7830	6.7	91
119	Low-temperature atomic layer deposition of ZnO thin films: Control of crystallinity and orientation. <i>Thin Solid Films</i> , 2011 , 519, 5319-5322	2.2	81
118	Controlling the crystallinity and roughness of atomic layer deposited titanium dioxide films. <i>Journal of Nanoscience and Nanotechnology</i> , 2011 , 11, 8101-7	1.3	45
117	Direct Writing of Channels for Microfluidics in Silica by MeV Ion Beam Lithography. <i>Advanced Materials Research</i> , 2011 , 254, 132-135	0.5	3

116	Atomic Layer Deposition of Ruthenium Films from (Ethylcyclopentadienyl)(pyrrolyl)ruthenium and Oxygen. <i>Journal of the Electrochemical Society</i> , 2011 , 158, D158	3.9	48
115	Atomic Layer Deposition and Characterization of Aluminum Silicate Thin Films for Optical Applications. <i>Journal of the Electrochemical Society</i> , 2011 , 158, P15	3.9	13
114	Porous inorganic-organic hybrid material by oxygen plasma treatment. <i>Journal of Micromechanics and Microengineering</i> , 2011 , 21, 125003	2	12
113	Corrosion Protection of Steel with Oxide Nanolaminates Grown by Atomic Layer Deposition. <i>Journal of the Electrochemical Society</i> , 2011 , 158, C369	3.9	51
112	Investigation of ZrO ₂ /HfO ₂ Based High-k Materials as Capacitor Dielectrics. <i>Journal of the Electrochemical Society</i> , 2010 , 157, G202	3.9	15
111	Atomic Layer Deposition and Characterization of Erbium Oxide-Doped Zirconium Oxide Thin Films. <i>Journal of the Electrochemical Society</i> , 2010 , 157, G193	3.9	10
110	Control of Oxygen Nonstoichiometry and Magnetic Property of MnCo ₂ O ₄ Thin Films Grown by Atomic Layer Deposition. <i>Chemistry of Materials</i> , 2010 , 22, 6297-6300	9.6	30
109	Atomic Layer Deposition of High-Permittivity Yttrium-Doped HfO ₂ Films. <i>Electrochemical and Solid-State Letters</i> , 2009 , 12, G1		27
108	Experimental Linear Energy Transfer of Heavy Ions in Silicon for RADEF Cocktail Species. <i>IEEE Transactions on Nuclear Science</i> , 2009 , 56, 2242-2246	1.7	14
107	Thin Film Characterisation Using MeV Ion Beams. <i>Particle Acceleration and Detection</i> , 2009 , 171-183	0.5	4
106	Aperture-edge scattering in MeV ion-beam lithography. I. Scattering from a straight Ta aperture edge. <i>Journal of Vacuum Science & Technology B</i> , 2009 , 27, 1101		4
105	Aperture-edge scattering in MeV ion-beam lithography. II. Scattering from a rectangular aperture. <i>Journal of Vacuum Science & Technology B</i> , 2009 , 27, 1109		7
104	Development of micro-contact printing of osteosarcoma cells using MeV ion beam lithography. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2009 , 267, 2306-2308	1.2	2
103	Considerations about multiple and plural scattering in heavy-ion low-energy ERDA. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2009 , 267, 1936-1941	1.2	2
102	Atomic layer deposition and characterization of biocompatible hydroxyapatite thin films. <i>Thin Solid Films</i> , 2009 , 517, 5819-5824	2.2	64
101	Influence of Substrate Bias on the Structural and Dielectric Properties of Magnetron-Sputtered Ba _x Sr _{1-x} TiO ₃ Thin Films. <i>Ferroelectrics</i> , 2009 , 392, 3-12	0.6	
100	Atomic layer deposition of lithium containing thin films. <i>Journal of Materials Chemistry</i> , 2009 , 19, 8767		75
99	Mobility determination of lead isotopes in glass for retrospective radon measurements. <i>Radiation Protection Dosimetry</i> , 2008 , 131, 212-6	0.9	3

98	Programmable proximity aperture lithography with MeV ion beams. <i>Journal of Vacuum Science & Technology B</i> , 2008 , 26, 1732		24
97	Elastic Recoil Detection Analysis 2008 ,		1
96	Low-energy heavy-ion TOF-ERDA setup for quantitative depth profiling of thin films. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2008 , 266, 5144-5150	1.2	33
95	Fabrication of microfluidic devices using MeV ion beam Programmable Proximity Aperture Lithography (PPAL). <i>Nuclear Instruments & Methods in Physics Research B</i> , 2008 , 266, 2461-2465	1.2	17
94	Wettability and compositional analysis of hydroxyapatite films modified by low and high energy ion irradiation. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2008 , 266, 2515-2519	1.2	11
93	Atomic layer deposition of polyimide thin films. <i>Journal of Materials Chemistry</i> , 2007 , 17, 664-669		111
92	Development of an MeV ion beam lithography system in Jyväskylä. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2007 , 260, 77-80	1.2	15
91	Growth of osteoblasts on lithographically modified surfaces. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2007 , 260, 130-135	1.2	14
90	Time-of-flight telescope for heavy-ion RBS. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2007 , 261, 529-533	1.2	3
89	Depth resolution optimization for low-energy ERDA. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2007 , 261, 512-515	1.2	10
88	Ion-sputtering deposition of CaF ₂ films for microscopic imaging of osteoblast cells. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2007 , 261, 719-722	1.2	3
87	Linear Energy Transfer of Heavy Ions in Silicon. <i>IEEE Transactions on Nuclear Science</i> , 2007 , 54, 1158-1162.	1.7	34
86	Resolution Performance of Programmable Proximity Aperture MeV Ion Beam Lithography System. <i>Materials Research Society Symposia Proceedings</i> , 2007 , 1020, 1		6
85	Atomic Layer Deposition and Properties of Lanthanum Oxide and Lanthanum-Aluminum Oxide Films. <i>Chemical Vapor Deposition</i> , 2006 , 12, 158-164		51
84	Overview of material re-deposition and fuel retention studies at JET with the Gas Box divertor. <i>Nuclear Fusion</i> , 2006 , 46, 350-366	3.3	85
83	Short-ranged structural rearrangement and enhancement of mechanical properties of organosilicate glasses induced by ultraviolet radiation. <i>Journal of Applied Physics</i> , 2006 , 99, 053511	2.5	109
82	The impact of the density and type of reactive sites on the characteristics of the atomic layer deposited WN _x Cy films. <i>Journal of Applied Physics</i> , 2006 , 99, 063515	2.5	8
81	HfO ₂ Films Grown by ALD Using Cyclopentadienyl-Type Precursors and H ₂ O or O ₃ as Oxygen Source. <i>Journal of the Electrochemical Society</i> , 2006 , 153, F39	3.9	33

80	Solid phase epitaxy of Na-ion irradiated Quartz: Cathodoluminescence, kinetics and surface morphology. <i>Journal of Non-Crystalline Solids</i> , 2006 , 352, 2986-2992	3.9	3
79	Irradiation-induced damage in porous low-k materials during low-energy heavy-ion elastic recoil detection analysis. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2006 , 249, 189-192	1.2	6
78	The analysis of a thin SiO ₂ /Si ₃ N ₄ /SiO ₂ stack: A comparative study of low-energy heavy ion elastic recoil detection, high-resolution Rutherford backscattering and secondary ion mass spectrometry. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2006 , 249, 847-850	1.2	9
77	Analysis of thin high-k and silicide films by means of heavy ion time-of-flight forward-scattering spectrometry. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2006 , 249, 292-296	1.2	6
76	Atomic layer deposition of calcium oxide and calcium hafnium oxide films using calcium cyclopentadienyl precursor. <i>Thin Solid Films</i> , 2006 , 500, 322-329	2.2	29
75	Effect of preparation conditions on properties of atomic layer deposited TiO ₂ films in MoO ₃ /TiO ₂ /Al stacks. <i>Thin Solid Films</i> , 2006 , 510, 39-47	2.2	14
74	Radical-Enhanced Atomic Layer Deposition of Metallic Copper Thin Films. <i>Journal of the Electrochemical Society</i> , 2005 , 152, G25	3.9	54
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51	Atomic layer deposition of HfO ₂ thin films and nanolayered HfO ₂ /Al ₂ O ₃ /Nb ₂ O ₅ dielectrics. <i>Journal of Materials Science: Materials in Electronics</i> , 2003 , 14, 361-367	2.1	29
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35	Comparison of hafnium oxide films grown by atomic layer deposition from iodide and chloride precursors. <i>Thin Solid Films</i> , 2002 , 416, 72-79	2.2	114
34	Properties of hafnium oxide films grown by atomic layer deposition from hafnium tetraiodide and oxygen. <i>Journal of Applied Physics</i> , 2002 , 92, 5698-5703	2.5	54
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